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Attorney for Applicants

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No.	:	10/849,348	Confirmation No.: 6690
Applicant	:	Robert H. Burgener, II et al.	
Title	:	GROUP II-VI SEMICONDUCTOR DEVICES	
Filed	:	May 19, 2004	
TC/A.U.	:	2814	
Examiner	:	Wai Sing Louie	
Docket No.	:	3398.2.10	
Customer No.	:	21552	

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL OF SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Transmitted herewith is an Information Disclosure Statement disclosing information which has come to the attention of applicants and/or their attorneys and is being submitted so as to comply with the duty of disclosure set forth in 37 C.F.R. § 1.56. In accordance with 37 C.F.R. § 1.97(c), the enclosed Statement is being filed before the mailing date of either a final action or a notice of allowance and is accompanied by credit card payment form in the amount of One Hundred Eighty Dollars ($180.00) to cover the fee set forth in 37 C.F.R. § 1.17(p).

Neither applicants nor their attorneys make any representation that any information disclosed herein may be "prior art" within the meaning of that term under 35 U.S.C. § 102 or § 103. Moreover, pursuant to 37 C.F.R. § 1.97, the filing of this Information Disclosure Statement

shall not be construed as a representation that a search has been made or as an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b).

In accordance with 37 C.F.R. § 1.98, transmitted herewith are:

1. A completed copy of Forms PTO/SB/08a and PTO/SB08b "Information Disclosure Statement by Applicant" listing the patents, publications and other information being submitted for consideration; and

2. A legible copy of each patent, publication and other item of information in written form listed on the enclosed Forms PTO/SB/08a and PTO/SB/08b, except for copies of U.S. patents and published U.S. patent applications which are not required for applications filed after June 30, 2003.

Respectfully submitted,

Evan R. Witt
Reg. No. 32,512
Attorney for Applicants

Date: October 3, 2005

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Sheet 1 Of 1

Complete if Known	
Application Number	10/849,348
Filing Date	May 19, 2004
First Named Inventor	Robert H. Burgener, II
Group Art Unit	2814
Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	U1	US-2004/0061114 A1	04/01/2004	Yan et al.	
	U2				
	U3				
	U4				
	U5				
	U6				
	U7				
	U8				
	U9				
	U10				
	U11				
	U12				
	U13				
	U14				

FOREIGN PATENT DOCUMENTS

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Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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First Named Inventor	Robert H. Burgener, II
Group Art Unit	2814
Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

	O15	WILKINSON, J., XIONG, G., UCER, K.B., and WILLIAMS, R.T.; Lifetime and Oscillator Strength of Excitonic Luminescence in Zinc Oxide; Department of Physics, Wake Forest University, Winston-Salem, NC.	
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Application Number	10/849,348
Filing Date	May 19, 2004
First Named Inventor	Robert H. Burgener, II
Group Art Unit	2814
Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

	O30	KOSSANYI, J., KOUYATE, D., POULIQUEN, J., RONFARD-HARET, J.C., VALAT, P., et al.; Photoluminescence of Semiconducting Zinc Oxide Containing Rare Earth Ions as Impurities; Journal of Luminescence; 1990; pp. 17-24; Vol. 46; Elsevier Science Publishers B.V. (north-Holland).	
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Attorney Docket Number	3398.2.10

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Attorney Docket Number	3398.2.10

	O62	NARAZAKI, A., TANAKA, K., HIRAO, K., HASHIMOTO, T., NASU, H., et al.; IR and XPS Studies on the Surface Structure of Poled ZnO-TeO_2 Glasses with Second-Order Nonlinearity; Journal of the American Ceramic Society; 2001; pp. 214-217; Vol. 84.	
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First Named Inventor	Robert H. Burgener, II
Group Art Unit	2814
Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

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First Named Inventor	Robert H. Burgener, II
Group Art Unit	2814
Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

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Examiner Name	Wai Sing Louie
Attorney Docket Number	3398.2.10

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Attorney Docket Number	3398.2.10

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